

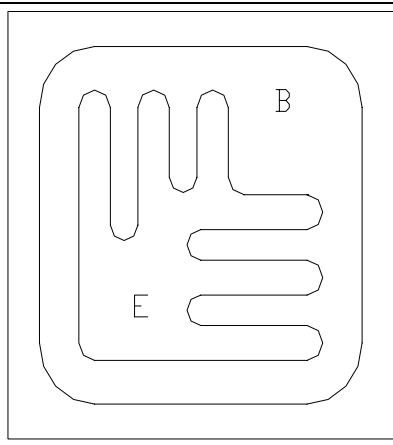
BC807A Silicon PNP Epitaxial Transistor

Description: The BC807A is designed for audio frequency general amplifier applications.

Features: ●Excellent h_{FE} Linearity

●Complementary to BC817A

Chip Appearance

	Chip Size		440um × 440um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	110um × 110um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		50um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-45V, I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1mA$	-50		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1mA$	-45		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1mA$	-5.0		V
DC Current Gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$	120	560	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.6	V